

COPPER ALLOY BONDING WIRE FOR SEMICONDUCTOR

ABSTRACT

The present invention is a copper-based bonding wire for use in a semiconductor element. The bonding wire of the present invention can be manufactured with an inexpensive material cost, and has a superior PCT reliability in a high-humidity/temperature environment. Further, the bonding wire of the present invention exhibits: a favorable TCT reliability through a thermal cycle test; a favorable press-bonded ball shape; a favorable wedge bondability; a favorable loop formability, and so on. Specifically, the bonding wire of the present invention is a copper alloy bonding wire for semiconductor manufactured by drawing a copper alloy containing 0.13 to 1.15% by mass of Pd and a remainder comprised of copper and unavoidable impurities.

No Fig.